

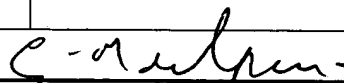
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Application Number				Filing Date				
First Named Inventor				Group Art Unit				
Examiner Name				Attorney Docket Number				
Sheet 1 of 1				November 26, 2001 Yoshiaki HASEGAWA et al. 740819-703				
U.S. PATENT DOCUMENTS								
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FOREIGN PATENT DOCUMENTS								
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		S. Ito et al., "Light Confinement of Ridge-geometry InGaN Laser Diode", Japanese Journal of Applied Physics 61, p. 325, 7p-L-4, September 2000 and English translation thereof.						
		Yves Lacroix et al., "Real-time etching depth monitoring for GaN-based laser diodes", Japanese Journal of Applied Physics 47, p. 378, 30a-YQ-7, March 2000.						
		S. Tanaka et al., "Nano-masking effects during GaN quantum dot formation", Japanese Journal of Applied Physics 46, P. 393, 28p-N-6, March 1999 and English translation thereof.						
		S. Tanaka et al., "Anti-Surfactant in III-Nitride Epitaxy-Quantum Dot Formation and Dislocation Termination", Japanese Journal of Applied Physics, Vol. 39, (2000), pp. L831-L834 Part 2, No. 8B, August 15, 2000.						
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